L	Hits	Search Text	DB	Time stamp
Number				
2	64606	(thin near film near transistor) TFT OTFT	USPAT;	2004/08/27
	1		US-PGPUB;	14:11
	1		EPO; JPO;	
	İ	·	DERWENT;	
			IBM_TDB	
4	283825	source and drain	USPAT;	2004/08/27
			US-PGPUB;	14:51
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	74579	(first near2 (insulat\$3 dielectric)) and	USPAT;	2004/08/27
	, 33/3	(second near2 (insulat\$3 dielectric))	US-PGPUB;	14:52
		(Second Hearz (Insuracys diefectife))	EPO; JPO;	14.52
			DERWENT;	
00	4720	//*\\daggerian = 64\\daggerian = \daggerian = \dagger	IBM_TDB	2004/00/07
22	4730	,,,	USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:53
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
		near2 (insulat\$3 dielectric)))	DERWENT;	
			IBM_TDB	
24	4110	(((::::::::::::::::::::::::::::::::::	USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:54
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
		near2 (insulat\$3 dielectric)))) and	DERWENT;	
		(@ad<20020923 @rlad<20020923)	IBM TDB	
25	4071		USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:54
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
		near2 (insulat\$3 dielectric)))) and	DERWENT;	
		(@ad<20020923 @rlad<20020923)) and gate	IBM TDB	
26	1889		USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:54
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	1 - 1 - 3 - 1
		near2 (insulat\$3 dielectric)))) and	DERWENT;	
			1	
		(@ad<20020923 @rlad<20020923)) and gate)	IBM_TDB	
	<u> </u>	and organic		<u> </u>

L	Hits	Search Text	DB	Time stamp
Number				
2	64606	(thin near film near transistor) TFT OTFT	USPAT;	2004/08/27
			US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	283825	source and drain	USPAT;	2004/08/27
1			US-PGPUB;	11:33
}			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
5	2906	(first near gate near (insulat\$3	USPAT;	2004/08/27
1		dielectric)) and (second near gate near	US-PGPUB;	11:35
		(insulat\$3 dielectric))	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
6	476	((thin near film near transistor) TFT	USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	11:35
		near gate near (insulat\$3 dielectric))	EPO; JPO;	
]		and (second near gate near (insulat\$3	DERWENT;	
		dielectric)))	IBM_TDB	